

In the Claims:

Please cancel Claims 16 and 17, without prejudice; add new Claim 18; and amend Claim 1 as indicated below. The status of all pending claims is as follows:

1. (Currently Amended) A pattern forming method for forming a resist pattern on a substrate having a plurality of divided exposure regions, the resist pattern extending across a first divided exposure region and a second divided exposure region among the plurality of divided exposure regions, the method comprising the steps of:

forming a resist film on the substrate;

exposing the resist film in the first divided exposure region to form a latent image which defines one edge of the resist pattern in the vicinity of a boundary between the first divided exposure region and the second divided exposure ~~region;~~ region, wherein the one edge is defined, in part, through the use of a first cutout portion, formed in a first mask, that extends in a first direction past a stitching portion and into the second divided exposure region;

exposing the resist film in the second divided exposure region to form a latent image which defines another edge of the resist pattern, opposite the one edge, in the vicinity of the ~~boundary or one edge of another resist pattern located opposite to that edge;~~ boundary, wherein the other edge is defined, in part, through the use of a second cutout portion, formed in a second mask, that extends in a second direction past the stitching portion and into the

first divided exposure region, where the second direction is opposite of the first direction;

and

developing the resist film to form the resist pattern.

2. (Original) A pattern forming method for forming a wiring pattern on a substrate having a plurality of divided exposure regions, the wiring pattern extending across a first divided exposure region and a second divided exposure region adjacent to each other among the plurality of divided exposure regions, the method comprising the steps of:

forming a wiring layer for forming the wiring pattern on the substrate;

forming a resist film on the wiring layer;

exposing the resist film in the first divided exposure region using a first exposure mask to form a latent image which defines one edge of the wiring pattern in the vicinity of a boundary between the first divided exposure region and the second divided exposure region;

exposing the resist film in the second divided exposure region using a second exposure mask to form a latent image which defines another edge of the wiring pattern in the vicinity of the boundary;

developing the resist film to form the resist pattern;

etching the wiring layer using the resist pattern as an etching mask to form the wiring pattern; and

correcting a relative misalignment of the first and second exposure masks relative to the substrate based on a pattern width of the wiring pattern formed in the vicinity of the boundary.

3. (Original) A pattern forming method according to claim 2, wherein the correction is made by measuring the pattern width of the wiring pattern and calculating the direction and amount of a misalignment of the first and second exposure masks relative to the substrate.

4. (Original) A method of manufacturing a thin film transistor substrate, comprising the steps of forming a plurality of bus lines extending on a substrate with an insulation film interposed; and forming a plurality of thin film transistors connected to any of the plurality of bus lines, wherein the bus lines are formed using the pattern forming method according to claim 1.

5. (Original) A method of manufacturing a thin film transistor substrate, comprising the steps of forming a plurality of bus lines extending on a substrate with an insulation film interposed; and forming a plurality of thin film transistors connected to any of the plurality of bus lines, wherein the bus lines are formed using the pattern forming method according to claim 2.

6. (Original) A method of manufacturing a thin film transistor substrate, comprising the steps of forming a plurality of bus lines extending on a substrate with an insulation film interposed; and forming a plurality of thin film transistors connected to any of the plurality of bus lines, wherein the bus lines are formed using the pattern forming method according to claim 3.

7. (Original) A method of manufacturing a thin film transistor substrate according to claim 4, wherein the bus lines are storage capacitor bus lines.

8. (Original) A method of manufacturing a thin film transistor substrate according to claim 5, wherein the bus lines are storage capacitor bus lines.

9. (Original) A method of manufacturing a thin film transistor substrate according to claim 6, wherein the bus lines are storage capacitor bus lines.

10. (Original) A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 4.

11. (Original) A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 5.

12. (Original) A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 6.

13. (Original) A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 7.

14. (Original) A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 8.

15. (Original) A method of manufacturing a liquid crystal display comprising a liquid crystal sealed between two substrates, wherein at least either of the two substrates is fabricated using the method of manufacturing a thin film transistor substrate according to claim 9.

16-17. (Canceled)

18. (New) A pattern forming method according to claim 1, wherein said first mask includes a first projection and said second mask includes a second projection, and further wherein during the step of exposing the resist film in the second divided exposure region, the second projection of the second mask is aligned to generally correspond with a previous position of the first cutout portion of the first mask and the second cutout portion of the second mask is aligned to generally correspond with a previous position of the first projection of the first mask.